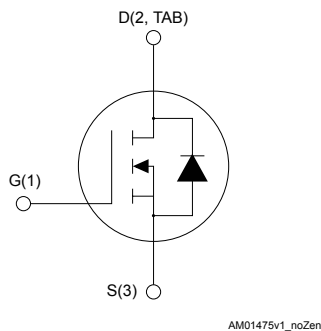
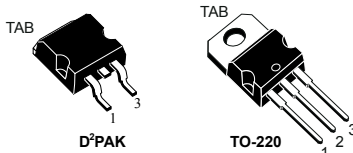



# Automotive-grade N-channel 60 V, 32 mΩ typ., 30 A STripFET II Power MOSFET in a D<sup>2</sup>PAK and TO-220 packages



## Features

Order codes	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STB36NF06LT4	60 V	40 mΩ	30 A
STP36NF06L	60 V	40 mΩ	30 A

- AEC-Q101 qualified 
- Exceptional dv/dt capability
- 100% avalanche tested
- Low gate charge

## Applications

- Switching applications

## Description

This Power MOSFET has been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.



### Product status links

[STB36NF06L](#)
[STP36NF06L](#)

### Product summary

Order code	STB36NF06LT4
Marking	B36NF06
Package	D <sup>2</sup> PAK
Packing	Tape and reel
Order code	STP36NF06L
Marking	P36NF06L
Package	TO-220
Packing	Tube

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0\text{ V}$ )	60	V
$V_{DGR}$	Drain-gate voltage ( $R_{GS} = 20\text{ k}\Omega$ )	60	V
$V_{GS}$	Gate-source voltage	$\pm 18$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	30	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	21	
$I_{DM}^{(1)}$	Drain current (pulsed)	120	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
	Derating factor	0.47	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	10	V/ns
$E_{AS}^{(3)}$	Single-pulse avalanche energy	225	mJ
$T_{stg}$	Storage temperature range	-55 to 175	$^\circ\text{C}$
$T_J$	Operating junction temperature range		$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 30\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq T_J\text{ max}$ .
3. Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $I_D = 15\text{ A}$ ,  $V_{DD} = 30\text{ V}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance, junction-to-case	2.14	$^\circ\text{C}/\text{W}$
$R_{thJA}$	Thermal resistance, junction-to-ambient	62.5	$^\circ\text{C}/\text{W}$
$T_I$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified.

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}, T_C = 125\text{ }^\circ\text{C}$			10	
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 18\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		32	40	m $\Omega$
		$V_{GS} = 5\text{ V}, I_D = 15\text{ A}$		45	50	

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}$	Forward transconductance	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$	-	15		S
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	660		pF
$C_{oss}$	Output capacitance		-	170		pF
$C_{rss}$	Reverse transfer capacitance		-	70		pF
$Q_g$	Total gate charge	$V_{DD} = 30\text{ V}, I_D = 30\text{ A}, V_{GS} = 5\text{ V}$ (see Figure 13. Test circuit for gate charge behavior)	-	13	17	nC
$Q_{gs}$	Gate-source charge		-	4.2		nC
$Q_{gd}$	Gate-drain charge		-	7.8		nC

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\text{ V}, I_D = 15\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 5\text{ V}$	-	10	-	ns
$t_r$	Rise time		-	80	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	19	-	ns
$t_f$	Fall time		-	13	-	ns

**Table 6. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		30	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		120	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 24\text{ A}, V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$	-	55		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 20\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	107		nC
$I_{RRM}$	Reverse recovery current	(see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	3.9		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

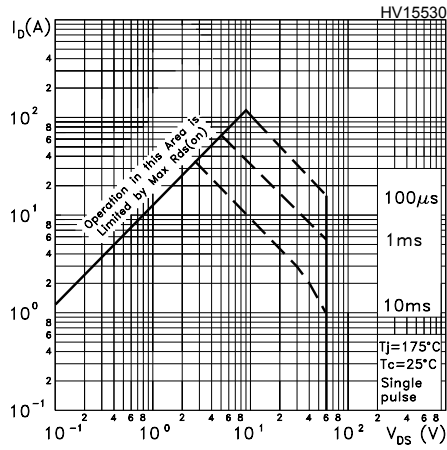


Figure 2. Thermal impedance

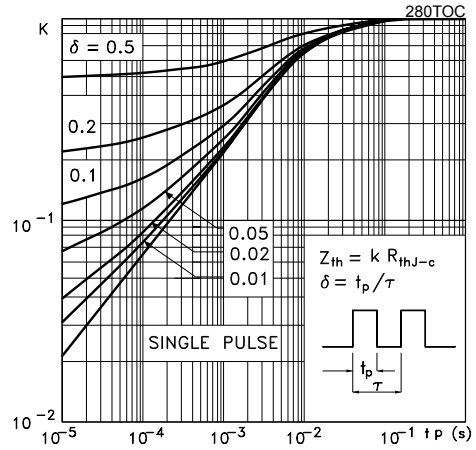


Figure 3. Output characteristics

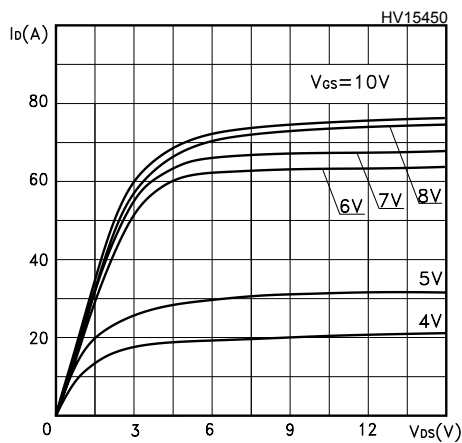


Figure 4. Transfer characteristics

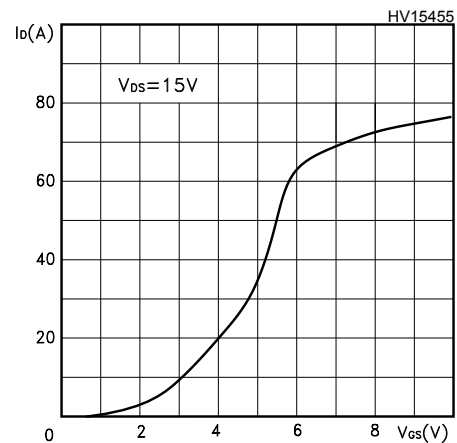


Figure 5. Transconductance

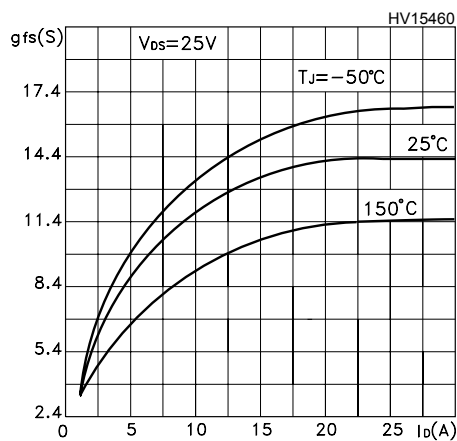
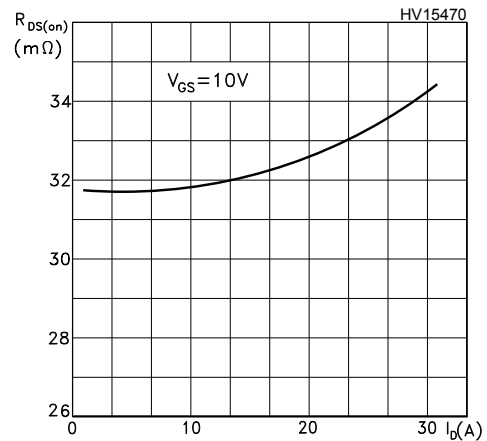
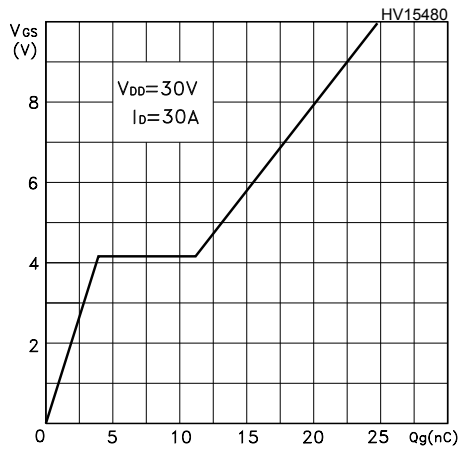


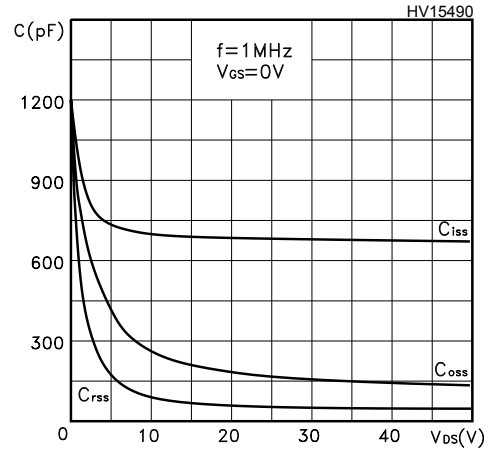
Figure 6. Static drain-source on-resistance



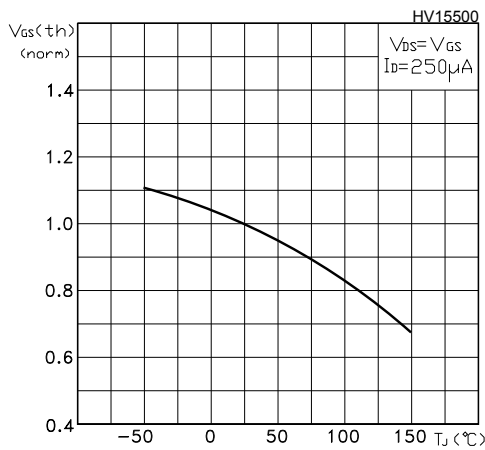
**Figure 7. Gate charge vs gate-source voltage**



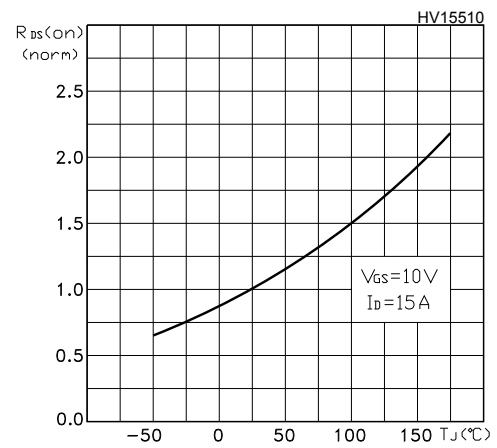
**Figure 8. Capacitance variations**



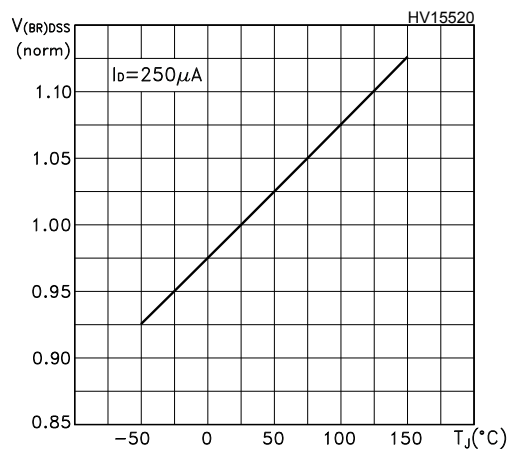
**Figure 9. Normalized gate threshold voltage vs temperature**



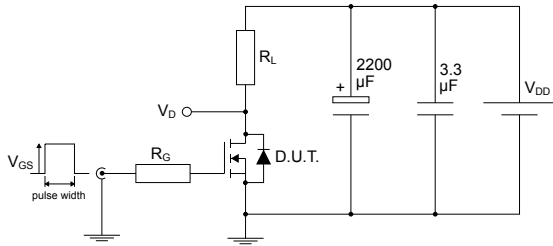
**Figure 10. Normalized on-resistance vs temperature**



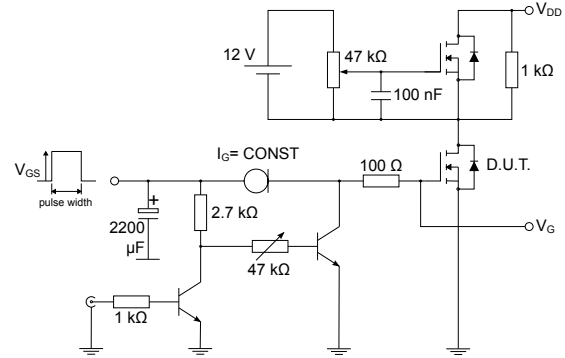
**Figure 11. Normalized  $V_{(BR)DSS}$  vs temperature**



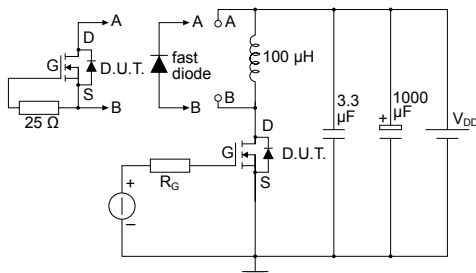
### 3 Test circuits

**Figure 12. Test circuit for resistive load switching times**


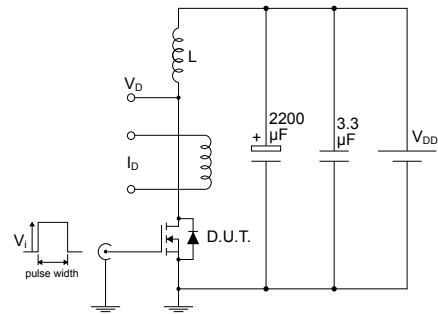
AM01468v1

**Figure 13. Test circuit for gate charge behavior**


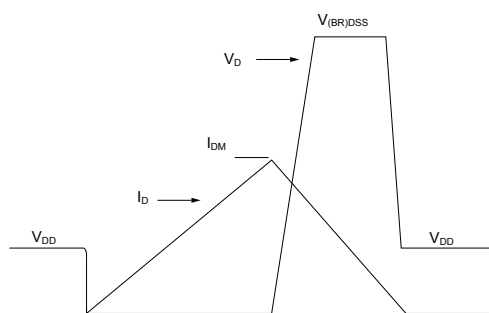
AM01469v1

**Figure 14. Test circuit for inductive load switching and diode recovery times**


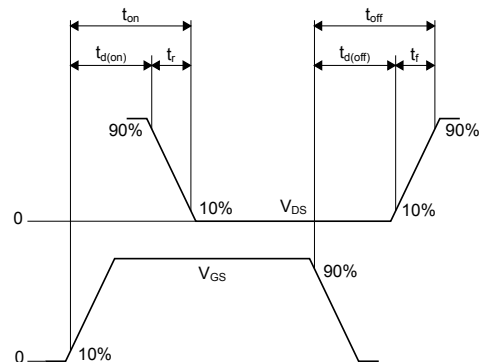
AM01470v1

**Figure 15. Unclamped inductive load test circuit**


AM01471v1

**Figure 16. Unclamped inductive waveform**


AM01472v1

**Figure 17. Switching time waveform**


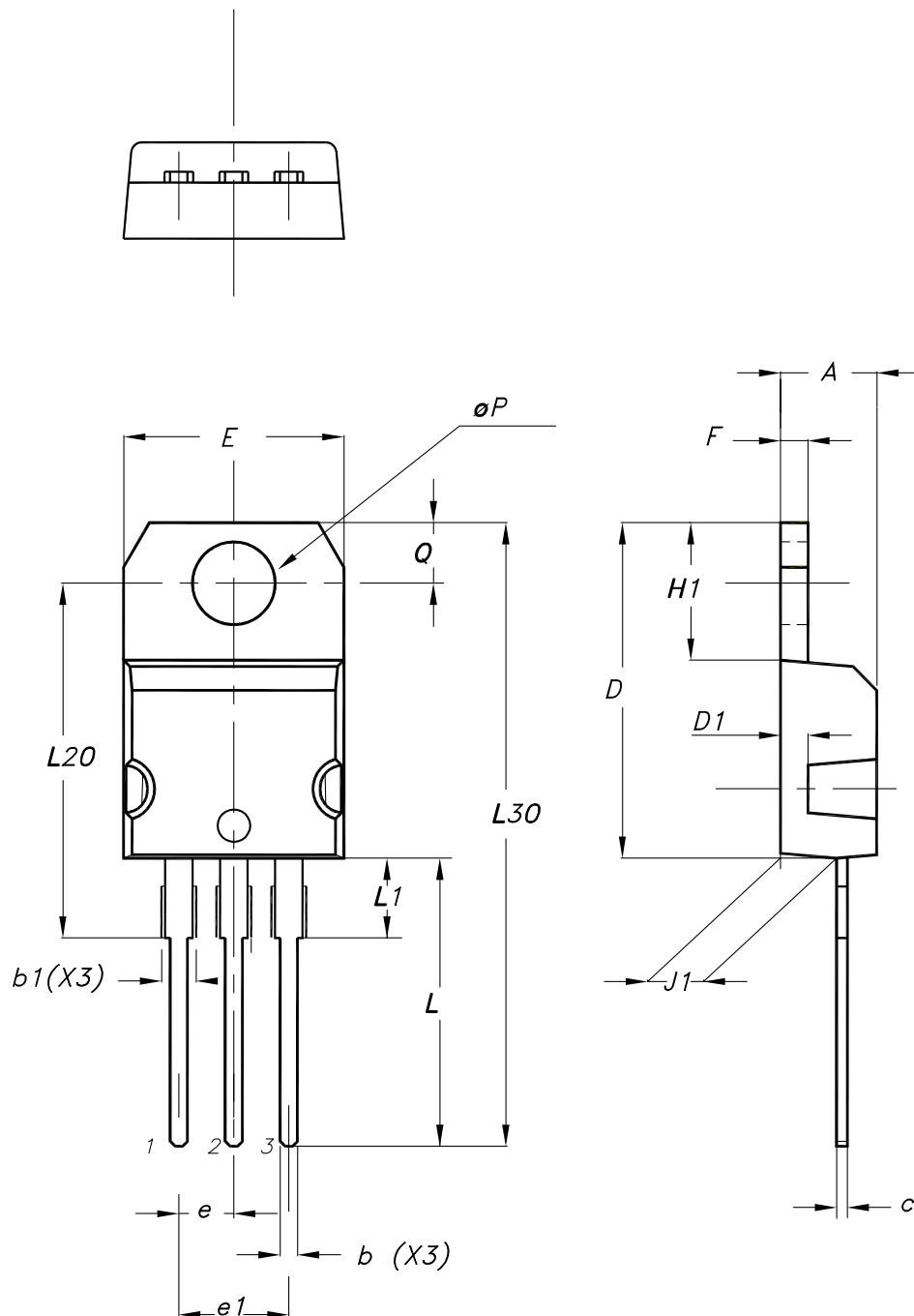
AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-220 type A package information

Figure 18. TO-220 type A package outline



0015988\_typeA\_Rev\_23

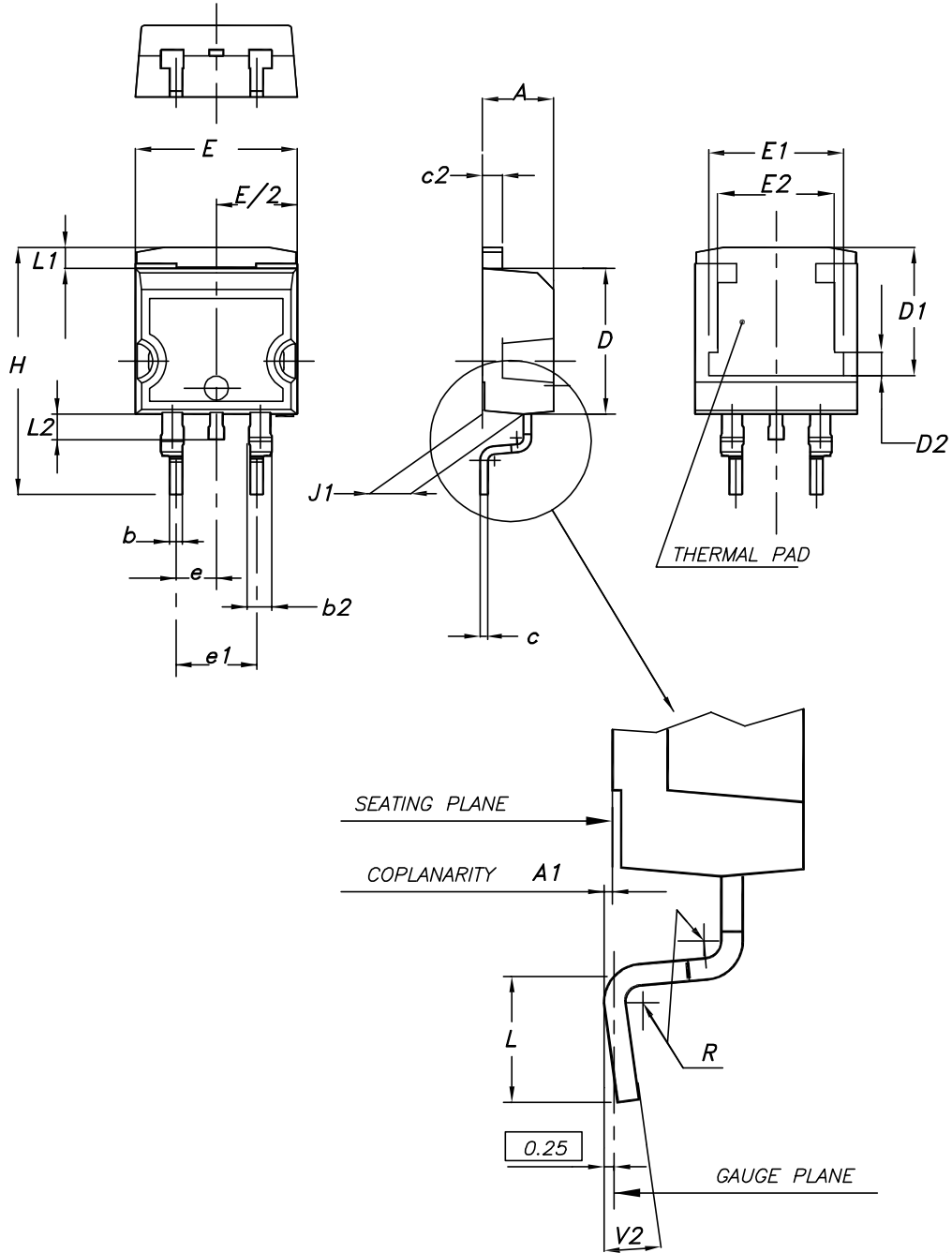


**Table 7. TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

## 4.2 D<sup>2</sup>PAK (TO-263) type A package information

Figure 19. D<sup>2</sup>PAK (TO-263) type A package outline

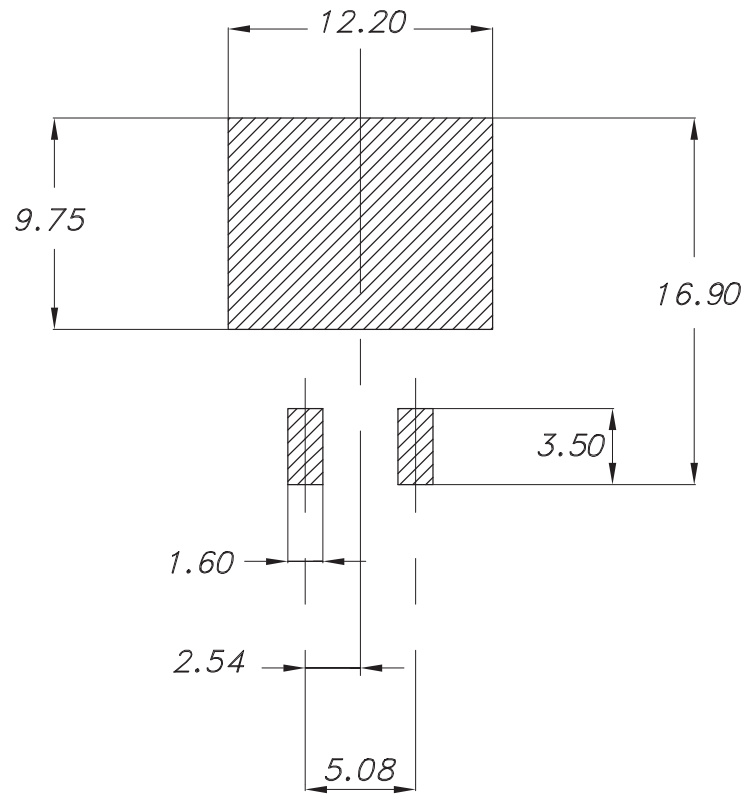


0079457\_26

**Table 8. D<sup>2</sup>PAK (TO-263) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

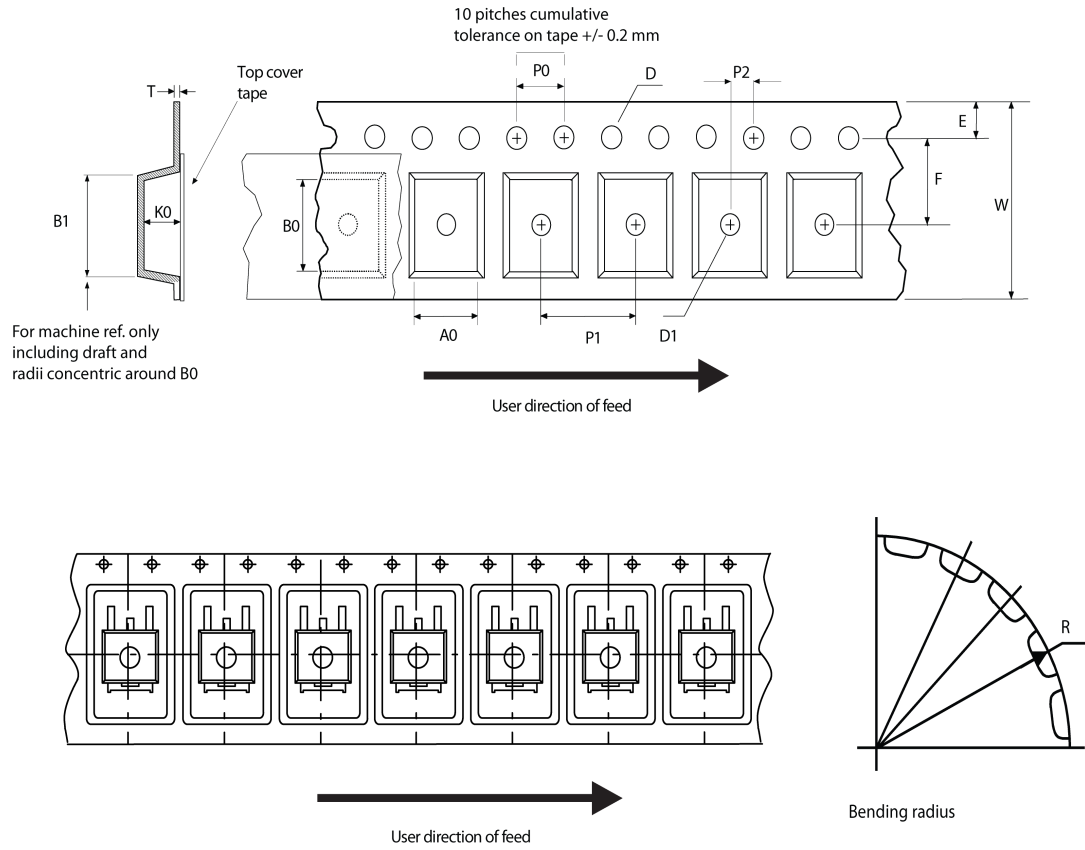
**Figure 20. D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)**



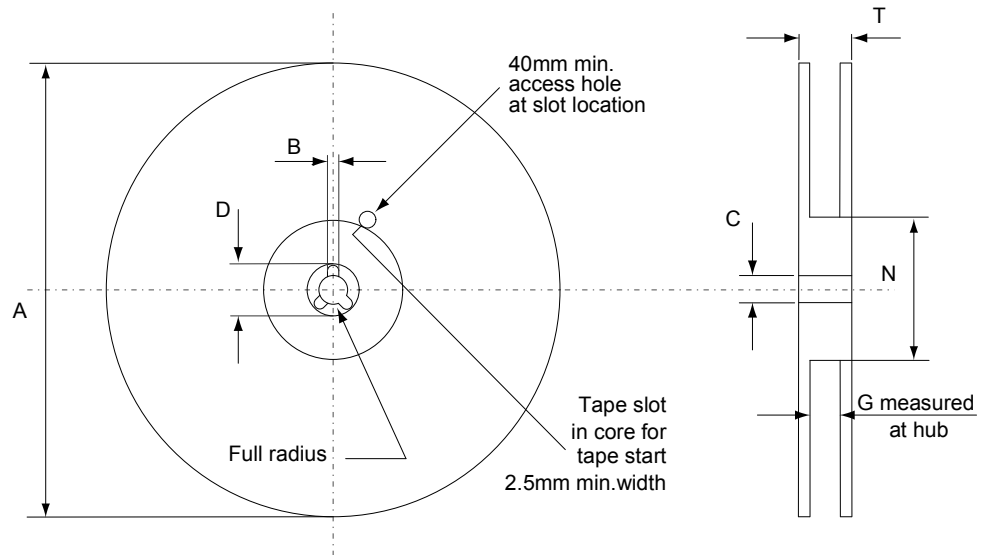
0079457\_Rev26\_footprint

### 4.3 D<sup>2</sup>PAK packing information

Figure 21. D<sup>2</sup>PAK tape outline



AM08852v1

**Figure 22. D<sup>2</sup>PAK reel outline**


AM06038v1

**Table 9. D<sup>2</sup>PAK tape and reel mechanical data**

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## Revision history

**Table 10. Document revision history**

Date	Version	Changes
14-Jun-2003	1	First release.
13-Mar-2006	2	Complete version.
26-Jun-2006	3	New template, no content change.
07-Oct-2022	4	Updated title, <a href="#">Internal schematic</a> , <a href="#">Device summary</a> , <a href="#">Features and Description</a> on cover page. Updated <a href="#">Section 4 Package information</a> . Minor text changes.

---

## Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>2</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>3</b>
<b>2.1</b>	Electrical characteristics (curves) .....	<b>5</b>
<b>3</b>	<b>Test circuits</b> .....	<b>7</b>
<b>4</b>	<b>Package information</b> .....	<b>8</b>
<b>4.1</b>	TO-220 type A package information .....	<b>8</b>
<b>4.2</b>	D <sup>2</sup> PAK (TO-263) type A package information .....	<b>10</b>
<b>4.3</b>	D <sup>2</sup> PAK packing information .....	<b>13</b>
	<b>Revision history</b> .....	<b>15</b>



**IMPORTANT NOTICE – READ CAREFULLY**

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgment.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. For additional information about ST trademarks, refer to [www.st.com/trademarks](http://www.st.com/trademarks). All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2022 STMicroelectronics – All rights reserved